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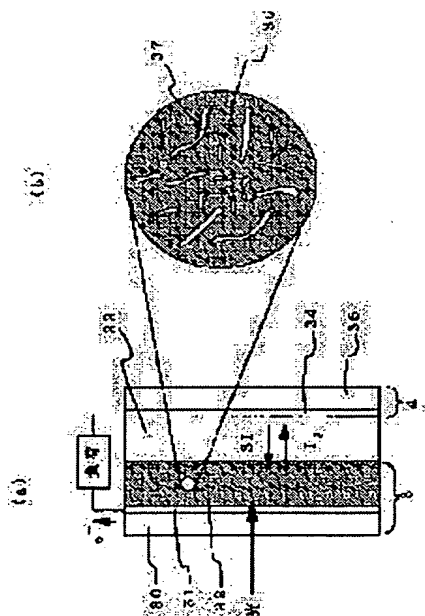
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### (54) SEMICONDUCTOR FOR PHOTOELECTRIC CONVERSION AND PHOTOELECTRIC CONVERSION ELEMENT



(57)Abstract:

PROBLEM TO BE SOLVED: To enhance photoelectric conversion efficiency by efficiently collecting electrons injected from coloring agent excited with light energy and increasing photoelectric current.

SOLUTION: A photoelectric transfer semiconductor 32 contains a metal phase 37 in at least one of the surface of a semiconductor particle and a space between semiconductor particles in the photoelectric conversion semiconductor 32 comprising a porous layer made from aggregated semiconductor particles and pigment, a photoelectric conversion semiconductor 42 comprises a porous layer made from aggregated metal particles 46 whose surfaces are made semi-conductive and a coloring agent, and the photoelectric conversion semiconductors 32, 42 are formed on conductive substrates 30, 31.

### LEGAL STATUS

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